TO-220F NPN Silicon NPN transistor in a TO-220F Plastic Package.

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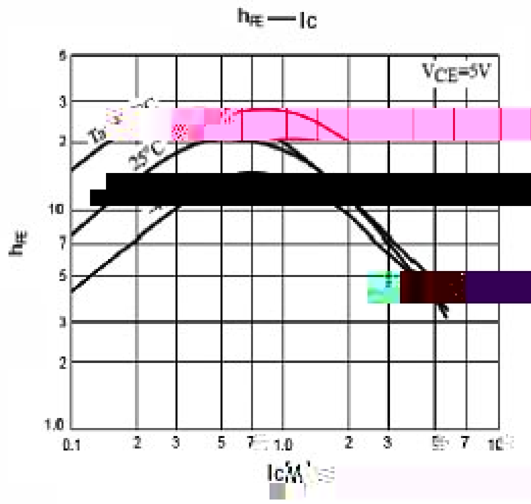
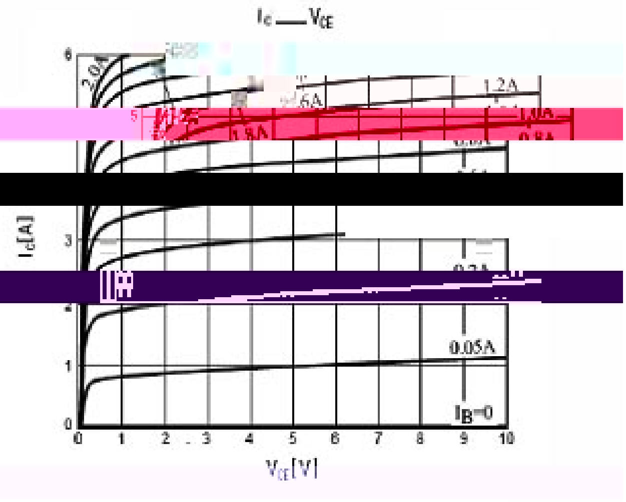
High breakdown voltage, Wide SOA, High switching speed, Low saturation voltage, Excellent current characteristics, Bulit-in dumper diode.

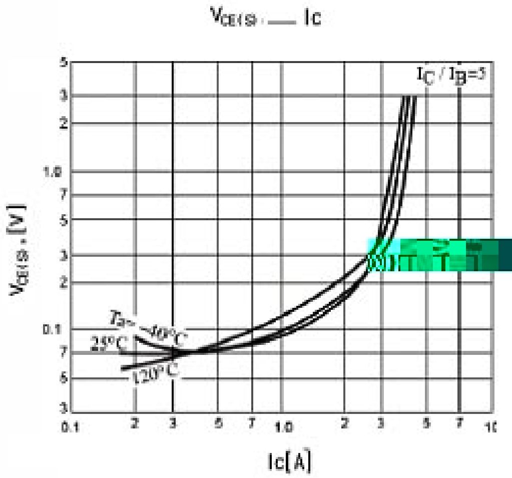
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage(V_{BE}=0)	V_{CES}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	6.0	A
Peak Collector Current	I_{CP}	15.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=25)	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

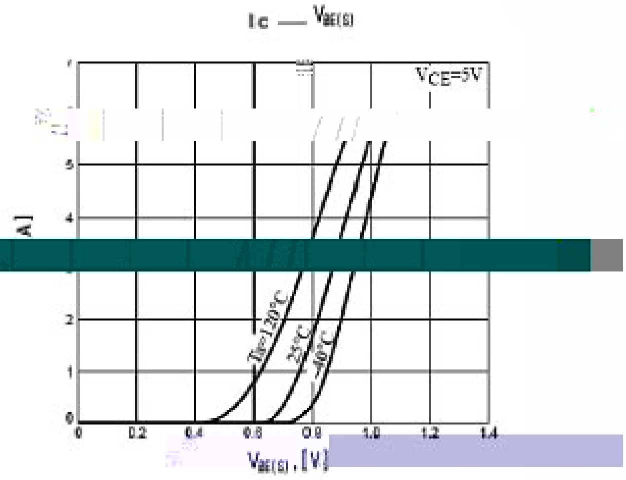
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=500mA I_C=0	5.0			V
Forward Voltage	V_F	I_F=3A			2.0	V
Collector Cut-Off Current	I_{CBO}	V_{CB}=1000V I_E=0			50	uA
		V_{CB}=1500V I_E=0			1.0	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4V				

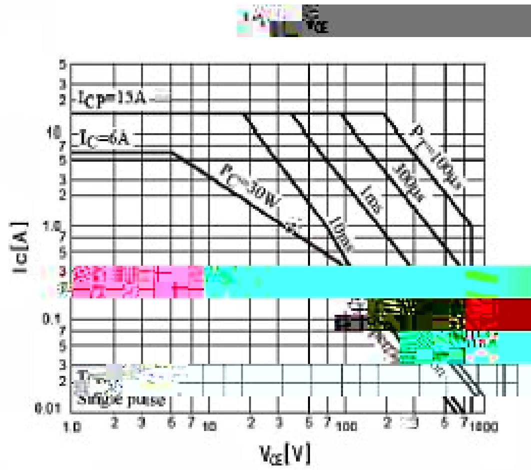
/ Electrical Characteristic Curve

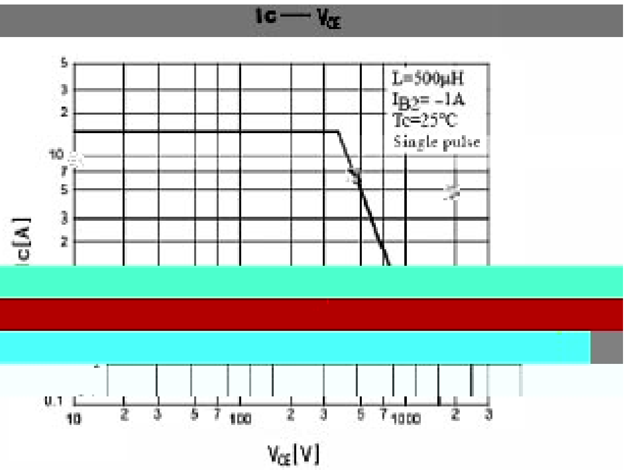




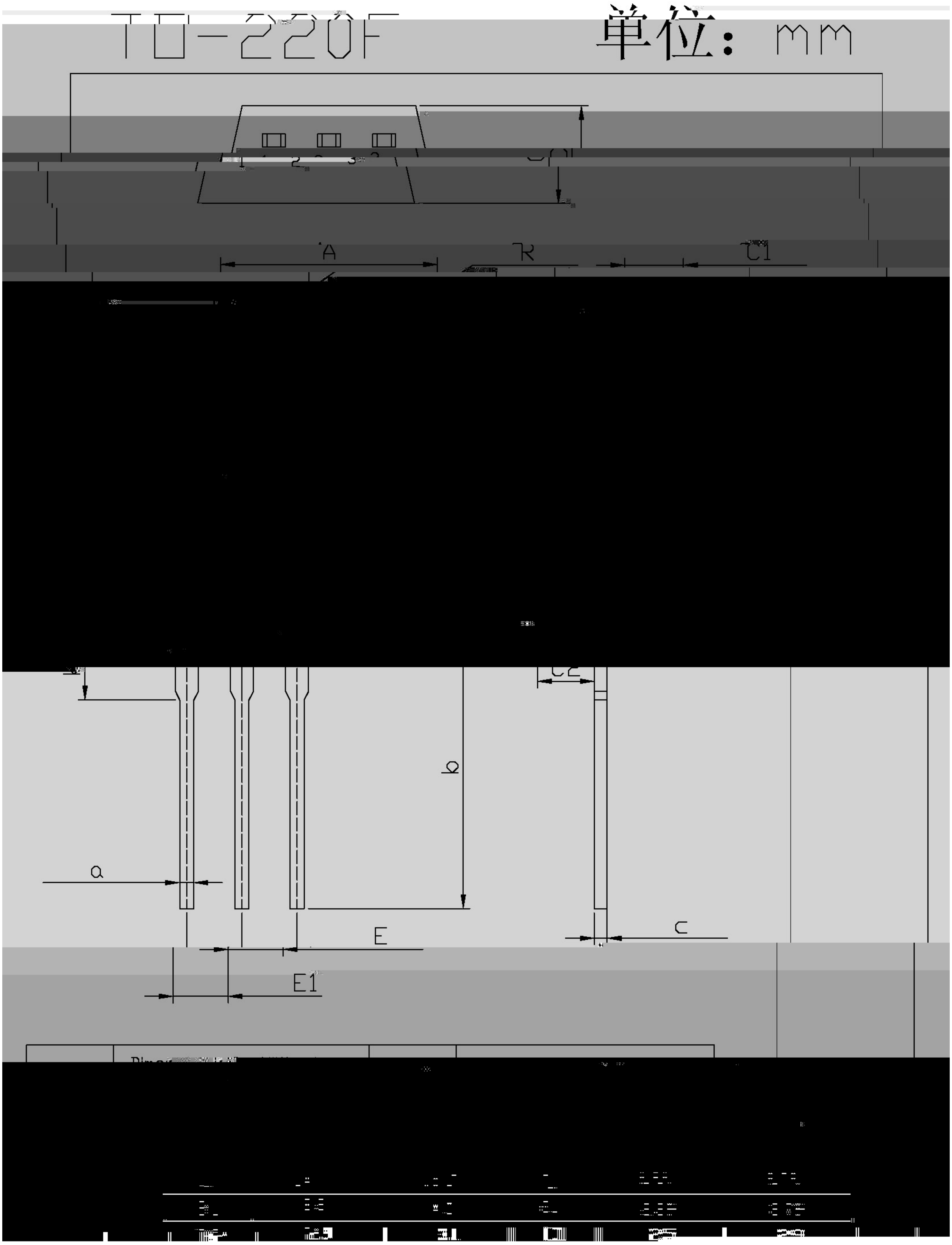




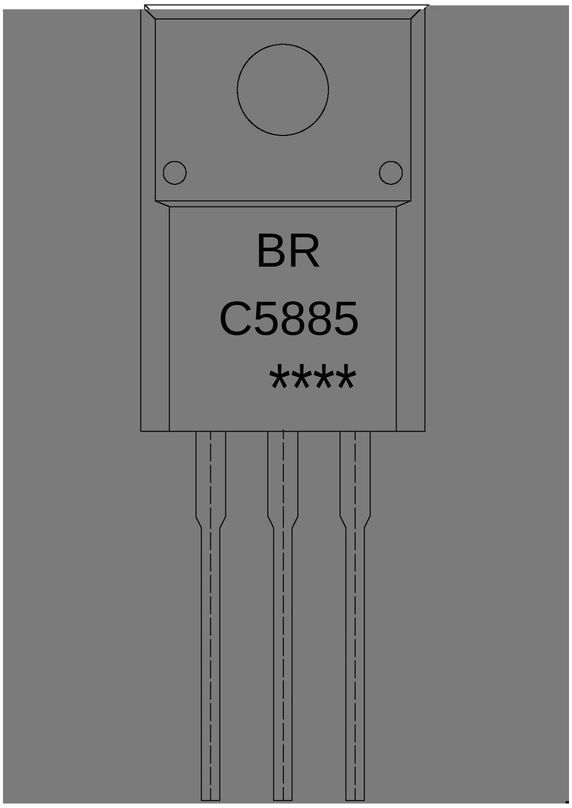




/ Package Dimensions



/ Marking Instructions



BR

C5885

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Note:

BR:	Company Code
C5885:	Product Type.
****:	Lot No. Code, code change with Lot No.